

TOSHIBA Transistor Silicon NPN·PNP Epitaxial Type  
(PCT process) (Bias Resistor built-in Transistor)

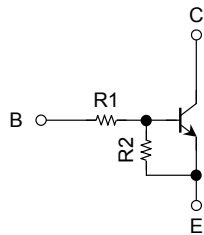
# RN4988FS

Switching, Inverter Circuit, Interface Circuit and  
Driver Circuit Applications

- Two devices are incorporated into a fine pitch Small Mold (6-pin) package.
- Incorporating a bias resistor into a transistor reduces parts count.  
Reducing the parts count enables the manufacture of ever more compact equipment and lowers assembly cost.

### Equivalent Circuit and Bias Resistor Values

**Q1**

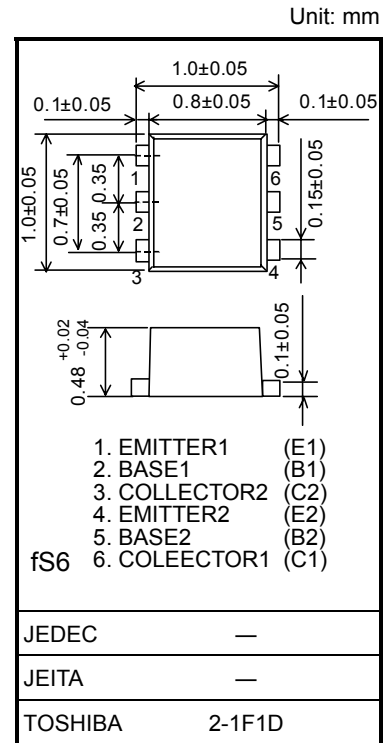
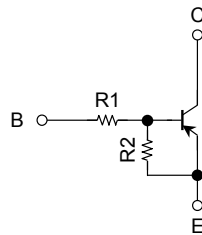


R1: 22 kΩ

R2: 47 kΩ

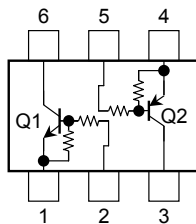
(Q1, Q2 common)

**Q2**

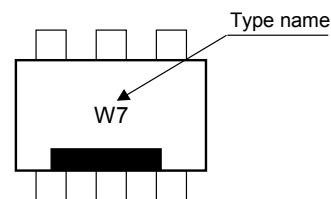


Weight:0.001g (typ.)

### Equivalent Circuit (top view)



### Marking



**Maximum Ratings (Ta = 25°C) (Q1)**

Characteristics	Symbol	Rating	Unit
Collector-base voltage	V <sub>CB0</sub>	20	V
Collector-emitter voltage	V <sub>CE0</sub>	20	V
Emitter-base voltage	V <sub>EB0</sub>	7	V
Collector current	I <sub>C</sub>	50	mA

**Maximum Ratings (Ta = 25°C) (Q2)**

Characteristics	Symbol	Rating	Unit
Collector-base voltage	V <sub>CB0</sub>	-20	V
Collector-emitter voltage	V <sub>CE0</sub>	-20	V
Emitter-base voltage	V <sub>EB0</sub>	-7	V
Collector current	I <sub>C</sub>	-50	mA

**Maximum Ratings (Ta = 25°C) (Q1, Q2 common)**

Characteristics	Symbol	Rating	Unit
Collector power dissipation	P <sub>C</sub> (Note)	50	mW
Junction temperature	T <sub>j</sub>	150	°C
Storage temperature range	T <sub>stg</sub>	-55~150	°C

Note: Total rating

**Electrical Characteristics (Ta = 25°C) (Q1)**

Characteristics	Symbol	Test Condition	Min	Typ.	Max	Unit
Collector cut-off current	$I_{CBO}$	$V_{CB} = 20\text{ V}, I_E = 0$	—	—	100	nA
	$I_{CEO}$	$V_{CE} = 20\text{ V}, I_B = 0$	—	—	500	
Emitter cut-off current	$I_{EBO}$	$V_{EB} = 7\text{ V}, I_C = 0$	0.085	—	0.126	mA
DC current gain	$h_{FE}$	$V_{CE} = 5\text{ V}, I_C = 10\text{ mA}$	120	—	—	
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C = 5\text{ mA}, I_B = 0.25\text{ mA}$	—	—	0.15	V
Input voltage (ON)	$V_{I(ON)}$	$V_{CE} = 0.2\text{ V}, I_C = 5\text{ mA}$	0.8	—	2.2	V
Input voltage (OFF)	$V_{I(OFF)}$	$V_{CE} = 5\text{ V}, I_C = 0.1\text{ mA}$	0.6	—	1.1	V
Collector output capacitance	$C_{ob}$	$V_{CB} = 10\text{ V}, I_E = 0, f = 1\text{ MHz}$	—	1.2	—	pF

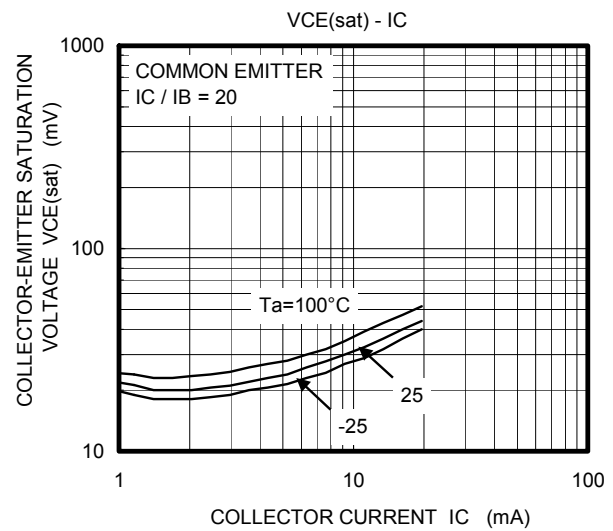
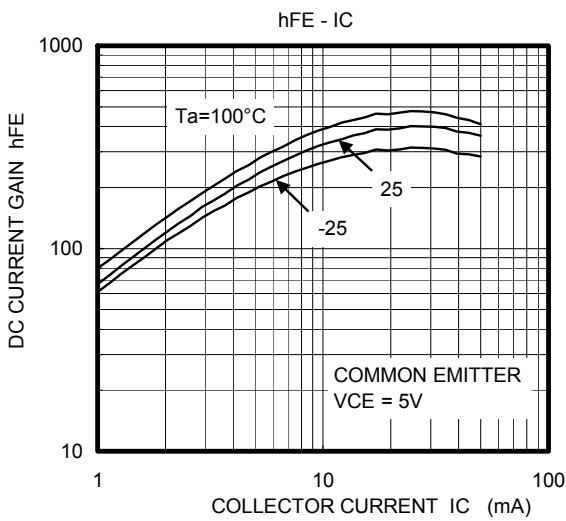
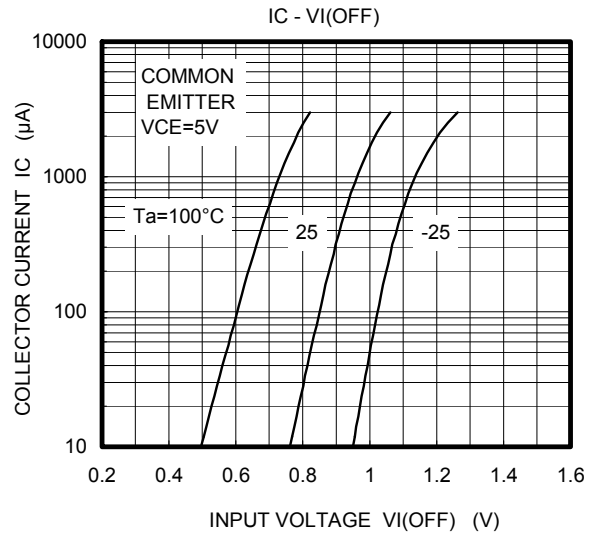
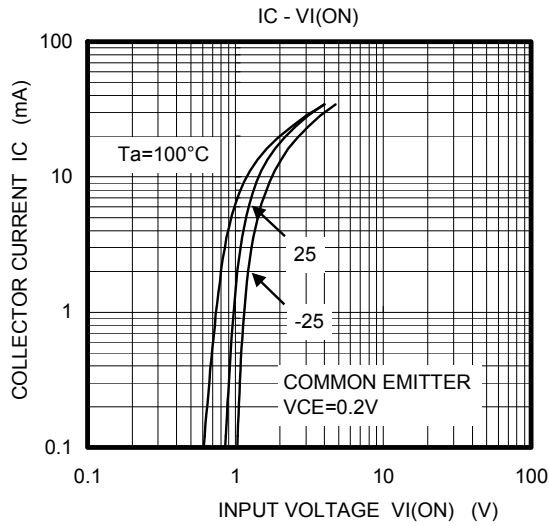
**Electrical Characteristics (Ta = 25°C) (Q2)**

Characteristics	Symbol	Test Condition	Min	Typ.	Max	Unit
Collector cut-off current	$I_{CBO}$	$V_{CB} = -20\text{ V}, I_E = 0$	—	—	-100	nA
	$I_{CEO}$	$V_{CE} = -20\text{ V}, I_B = 0$	—	—	-500	
Emitter cut-off current	$I_{EBO}$	$V_{EB} = -7\text{ V}, I_C = 0$	-0.085	—	-0.126	mA
DC current gain	$h_{FE}$	$V_{CE} = -5\text{ V}, I_C = -10\text{ mA}$	120	—	—	
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C = -5\text{ mA}, I_B = -0.25\text{ mA}$	—	—	-0.15	V
Input voltage (ON)	$V_{I(ON)}$	$V_{CE} = -0.2\text{ V}, I_C = -5\text{ mA}$	-0.8	—	-2.2	V
Input voltage (OFF)	$V_{I(OFF)}$	$V_{CE} = -5\text{ V}, I_C = -0.1\text{ mA}$	-0.6	—	-1.1	V
Collector output capacitance	$C_{ob}$	$V_{CB} = -10\text{ V}, I_E = 0, f = 1\text{ MHz}$	—	1.2	—	pF

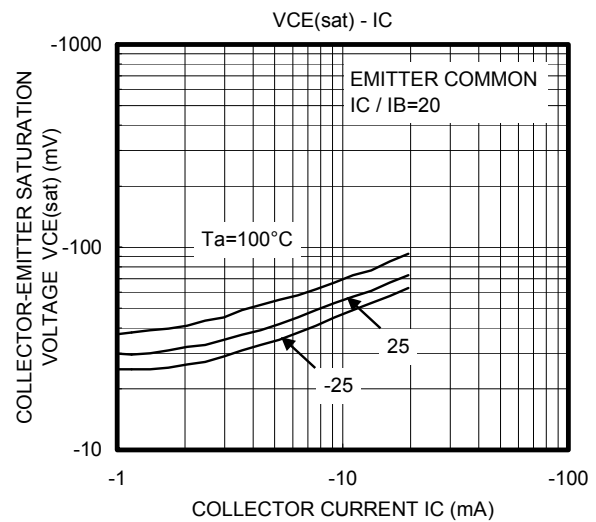
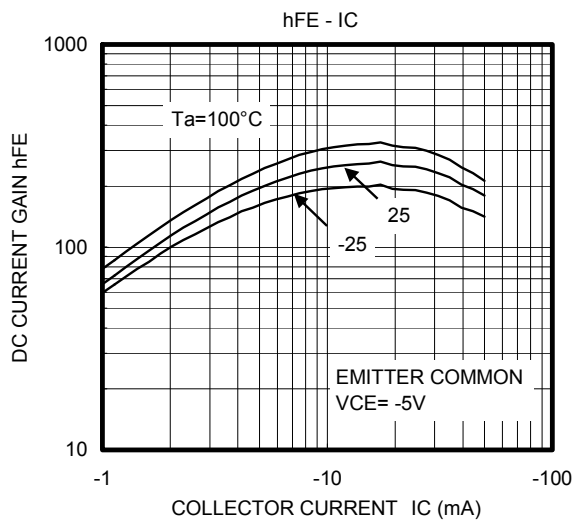
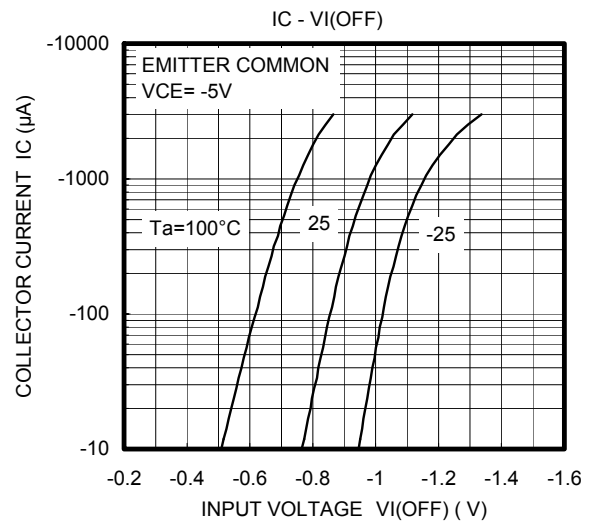
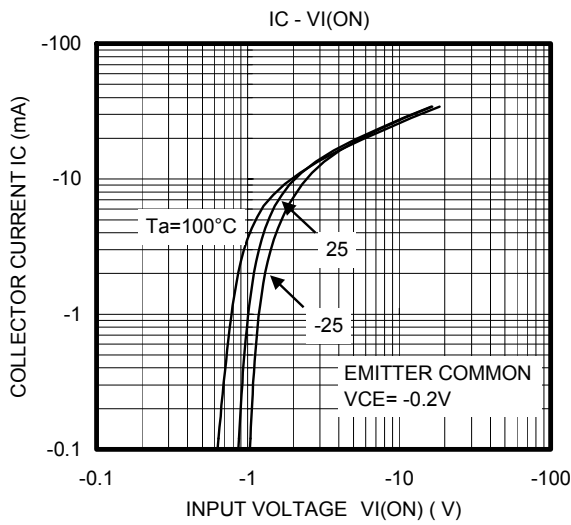
**Electrical Characteristics (Ta = 25°C) (Q1, Q2 common)**

Characteristics	Symbol	Test Condition	Min	Typ.	Max	Unit
Input resistor	R1	—	17.6	22	26.4	kΩ
Resistor ratio	R1/R2	—	0.374	0.468	0.562	

Q1



Q2



**HANDLING PRECAUTION**

Before handling individual devices that are not yet mounted on a circuit board, make sure that the environment is protected against static electricity. Operators should wear anti-static clothing, and containers and other objects that come direct contact with devices should be made of anti-static materials.

**RESTRICTIONS ON PRODUCT USE**

030619EAA

- The information contained herein is subject to change without notice.
- The information contained herein is presented only as a guide for the applications of our products. No responsibility is assumed by TOSHIBA for any infringements of patents or other rights of the third parties which may result from its use. No license is granted by implication or otherwise under any patent or patent rights of TOSHIBA or others.
- TOSHIBA is continually working to improve the quality and reliability of its products. Nevertheless, semiconductor devices in general can malfunction or fail due to their inherent electrical sensitivity and vulnerability to physical stress. It is the responsibility of the buyer, when utilizing TOSHIBA products, to comply with the standards of safety in making a safe design for the entire system, and to avoid situations in which a malfunction or failure of such TOSHIBA products could cause loss of human life, bodily injury or damage to property.  
In developing your designs, please ensure that TOSHIBA products are used within specified operating ranges as set forth in the most recent TOSHIBA products specifications. Also, please keep in mind the precautions and conditions set forth in the "Handling Guide for Semiconductor Devices," or "TOSHIBA Semiconductor Reliability Handbook" etc..
- The TOSHIBA products listed in this document are intended for usage in general electronics applications (computer, personal equipment, office equipment, measuring equipment, industrial robotics, domestic appliances, etc.). These TOSHIBA products are neither intended nor warranted for usage in equipment that requires extraordinarily high quality and/or reliability or a malfunction or failure of which may cause loss of human life or bodily injury ("Unintended Usage"). Unintended Usage include atomic energy control instruments, airplane or spaceship instruments, transportation instruments, traffic signal instruments, combustion control instruments, medical instruments, all types of safety devices, etc.. Unintended Usage of TOSHIBA products listed in this document shall be made at the customer's own risk.
- TOSHIBA products should not be embedded to the downstream products which are prohibited to be produced and sold, under any law and regulations.